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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/822,378	04/12/2004	Hong-Rae Kim	8028-40 (SPX200306-0018US	2840
22150 75	590 08/22/2005		EXAM	INER .
F. CHAU & ASSOCIATES, LLC 130 WOODBURY ROAD			SMITH, BRADLEY	
WOODBURY, NY 11797			ART UNIT	PAPER NUMBER
			2891	:
			DATE MAILED: 08/22/2005	
				:

Please find below and/or attached an Office communication concerning this application or proceeding.

		<u></u>				
	Application No.	Applicant(s)				
	10/822,378	KIM ET AL.				
Office Action Summary	Examiner	Art Unit				
	Bradley K. Smith	2891				
The MAILING DATE of this communication Period for Reply	appears on the cover sheet with the	correspondence address				
A SHORTENED STATUTORY PERIOD FOR RE THE MAILING DATE OF THIS COMMUNICATIO - Extensions of time may be available under the provisions of 37 CFF after SIX (6) MONTHS from the mailing date of this communication - If the period for reply specified above is less than thirty (30) days, a - If NO period for reply is specified above, the maximum statutory per - Failure to reply within the set or extended period for reply will, by standard patent term adjustment. See 37 CFR 1.704(b).	N). R 1.136(a). In no event, however, may a reply be to . reply within the statutory minimum of thirty (30) deriod will apply and will expire SIX (6) MONTHS fro atute, cause the application to become ABANDON	timely filed ays will be considered timely. m the mailing date of this communication. IED (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on _	·					
2a) This action is FINAL . 2b) ⊠ 1						
3) Since this application is in condition for allo closed in accordance with the practice under						
Disposition of Claims						
4)⊠ Claim(s) 1-22 is/are pending in the application.						
	4a) Of the above claim(s) is/are withdrawn from consideration.					
5)⊠ Claim(s) <u>13-22</u> is/are allowed.						
6)⊠ Claim(s) <u>1,6,7 and 12</u> is/are rejected.						
7)⊠ Claim(s) 2-5 and 8-11 is/are objected to.						
8) Claim(s) are subject to restriction an	d/or election requirement.	•				
Application Papers						
9)⊠ The specification is objected to by the Exam	niner.					
D)⊠ The drawing(s) filed on <u>12 April 2004</u> is/are: a)⊠ accepted or b)□ objected to by the Examiner.						
Applicant may not request that any objection to		-				
Replacement drawing sheet(s) including the con						
11) The oath or declaration is objected to by the	Examiner. Note the attached Offic	e Action or form PTO-152.				
Priority under 35 U.S.C. § 119						
12)⊠ Acknowledgment is made of a claim for fore a)⊠ All b)□ Some * c)□ None of:		a)-(d) or (f).				
1. Certified copies of the priority documents have been received.						
2. Certified copies of the priority docume	• •					
3. Copies of the certified copies of the p		ved in this National Stage				
application from the International Bur						
* See the attached detailed Office action for a	list of the certified copies not receiv	ed.				
Attachment(s)						
1) 💆 Notice of References Cited (PTO-892)	4) 🔲 Interview Summar					
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail E	Date Patent Application (PनO-152)				
Information Disclosure Statement(s) (PTO-1449 or PTO/SB/Paper No(s)/Mail Date	6) Other: search note					

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DETAILED ACTION

Information Disclosure Statement

1. The listing of references in the specification is not a proper information disclosure statement. 37 CFR 1.98(b) requires a list of all patents, publications, or other information submitted for consideration by the Office, and MPEP § 609 A(1) states, "the list may not be incorporated into the specification but must be submitted in a separate paper." Therefore, unless the references have been cited by the examiner on form PTO-892, they have not been considered.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claims 1, 6, 7 and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Heo et al. (US Patent 6,756,654) in view of Park et al. (US 2002/0076900). Heo et al. disclose providing a semiconductor substrate having a cell array region and a peripheral region, forming at least one cell trench in the cell array region and at least one peripheral trench wider than the cell trench in the peripheral region of the substrate, wherein the cell and the peripheral trenches have sidewalls; forming a first dielectric layer that partially fills the cell trench and the peripheral trench over the substrate; forming at least one photoresist pattern that exposes at least the peripheral trench partially filled with the first dielectric layer over the substrate; etching

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the first dielectric layer formed on the sidewalls of the exposed peripheral trench using the photoresist pattern as a etch mask; removing the photoresist pattern, and forming a second dielectric layer filling the cell trench and the peripheral trench over the substrate where the photoresist pattern is removed (see figures 6-8). With regards to claim 6 Heo et al. disclose forming the first capping layer of a thermal oxide. With regards to claim 12 the second dielectric is made of USG or HDP (see column 7 lines 10-20). However Heo et al. fails to disclose the formation of the photoresist over the peripheral trench and in order to etch the cell trench. Whereas Park et al. disclose forming a photoresist over a peripheral trench in order to etch the cell trench (see figure 3d). Therefore it would have been obvious to one of ordinary skill in the art at the time the invention was made to combine the teachings of Heo et al. and Park et al. because etching the cell trench would enable one to deposit a second dielectric layer without voids.

Allowable Subject Matter

- 4. Claim13-22 are allowed.
- 5. Claims 2-5,8-11 objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- 6. The following is a statement of reasons for the indication of allowable subject matter: the prior art of record niether teaches nor suggests forming the gate dielectric polish stop and hard mask before the formation of the trench (claims 2-5 and 13-22), the

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first dielectric is made of hdp cvd oxide, using the wet etch process for the cell trench sidewalls (claim 9), forming the second capping layer (claims 10 and 11).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Bradley K. Smith whose telephone number is (571) 272
7.

1884. The examiner can normally be reached on 10-6 Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Bill Baumeister can be reached on (571) 272-1722. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

BRADLEY K. SMITH PRIMARY EXAMINER